ON Semiconductor

Is Now

To learn more about onsemi™, please visit our website at www.onsemi.com

MPSA20

Amplifier Transistor

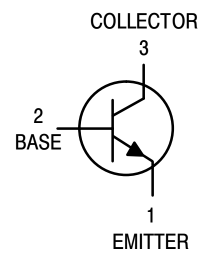
NPN Silicon

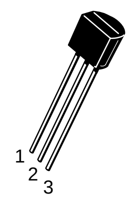
Features

- Pb−Free Package is Available*

ON Semiconductor®

http://onsemi.com





TO−92
CASE 29−11
STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	40	Vdc
Collector − Base Voltage	V_{CBO}	4.0	Vdc
Collector Current − Continuous	I_C	100	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0	mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

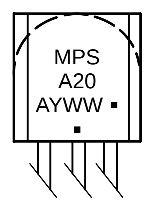
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.

MARKING DIAGRAM



MPSA20 = Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping
MPSA20	TO−92	5,000 Units / Box
MPSA20G	TO−92 (Pb−Free)	5,000 Units / Box

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

January, 2006 − Rev. 3

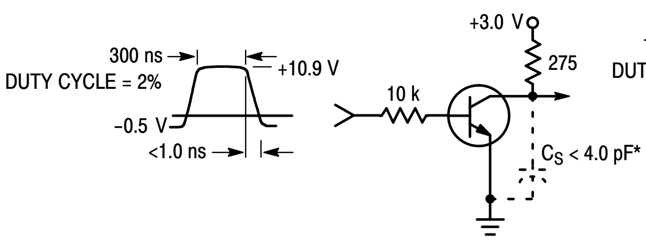
Publication Order Number:
MPSA20/D

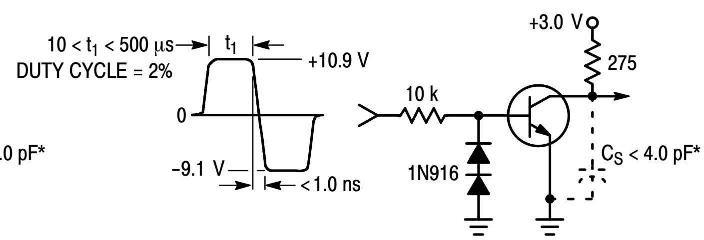
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector−Emitter Breakdown Voltage (Note 2) (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	40	−	Vdc
Emitter−Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	4.0	−	Vdc
Collector Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	−	100	nAdc
ON CHARACTERISTICS				
DC Current Gain (Note 2) (I_C = 5.0 mAdc, V_{CE} = 10 Vdc)	h_{FE}	40	400	−
Collector−Emitter Saturation Voltage (I_C = 10 mAdc, I_B = 1.0 mAdc)	$V_{CE(sat)}$	−	0.25	Vdc
SMALL−SIGNAL CHARACTERISTICS				
Current−Gain − Bandwidth Product (Note 2) (I_C = 5.0 mAdc, V_{CE} = 10 Vdc, f = 100 MHz)	f_T	125	−	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	−	4.0	pF

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

EQUIVALENT SWITCHING TIME TEST CIRCUITS





*Total shunt capacitance of test jig and connectors

Figure 1. Turn−On Time

Figure 2. Turn−Off Time

NOISE FIGURE CONTOURS

(V_{CE} = 5.0 Vdc, T_A = 25°C)

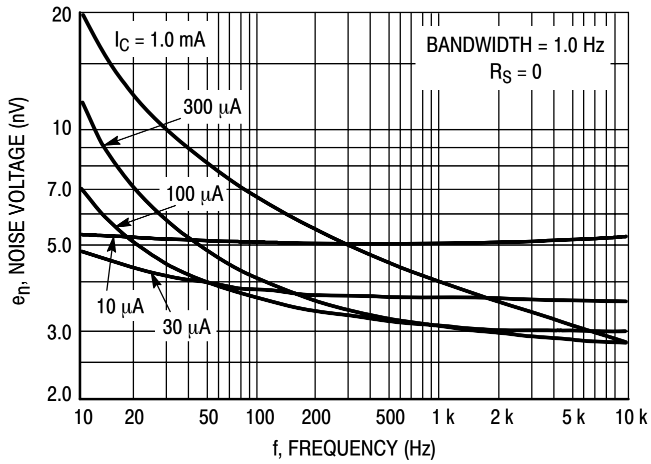


Figure 3. Noise Voltage

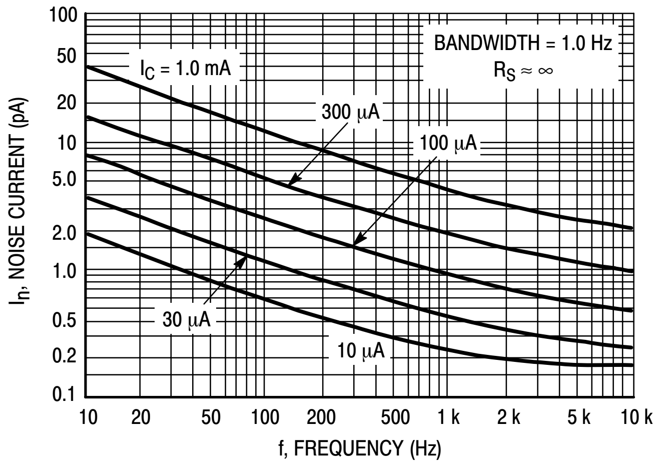


Figure 4. Noise Current

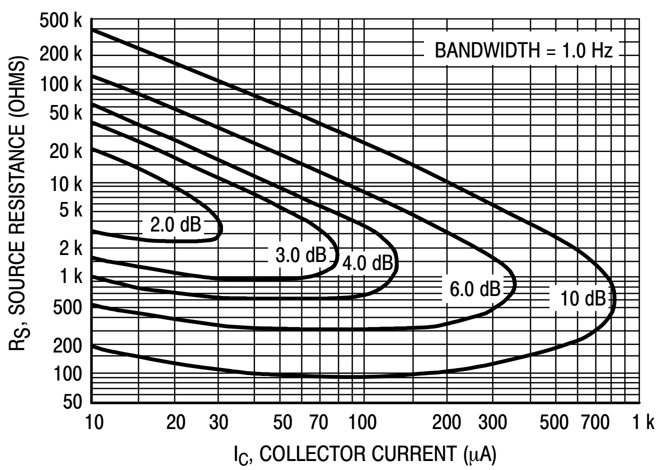


Figure 5. Narrow Band, 100 Hz

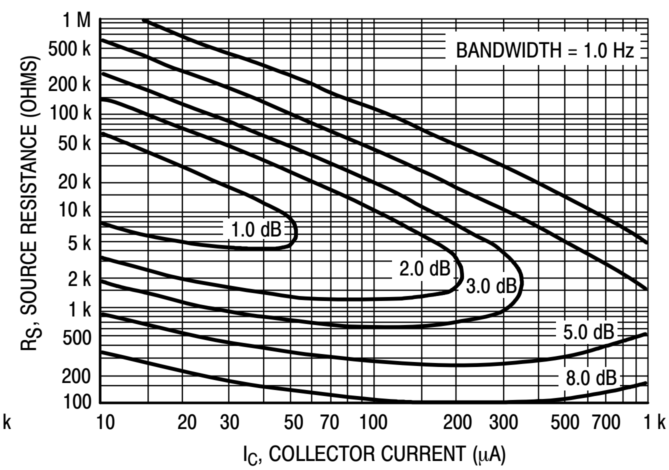


Figure 6. Narrow Band, 1.0 kHz

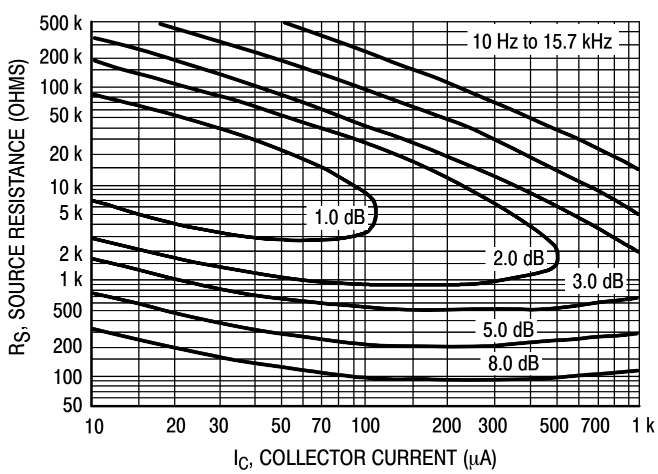


Figure 7. Wideband

Noise Figure is defined as:

$$NF = 20 \log_{10}\left(\frac{e_n{}^2 + 4KTR_S + I_n{}^2 R_S{}^2}{4KTR_S}\right)^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)
I_n = Noise Current of the Transistor referred to the input. (Figure 4)
K = Boltzman's Constant (1.38 x 10^{-23} j/°K)
T = Temperature of the Source Resistance (°K)
R_S = Source Resistance (Ohms)

TYPICAL STATIC CHARACTERISTICS

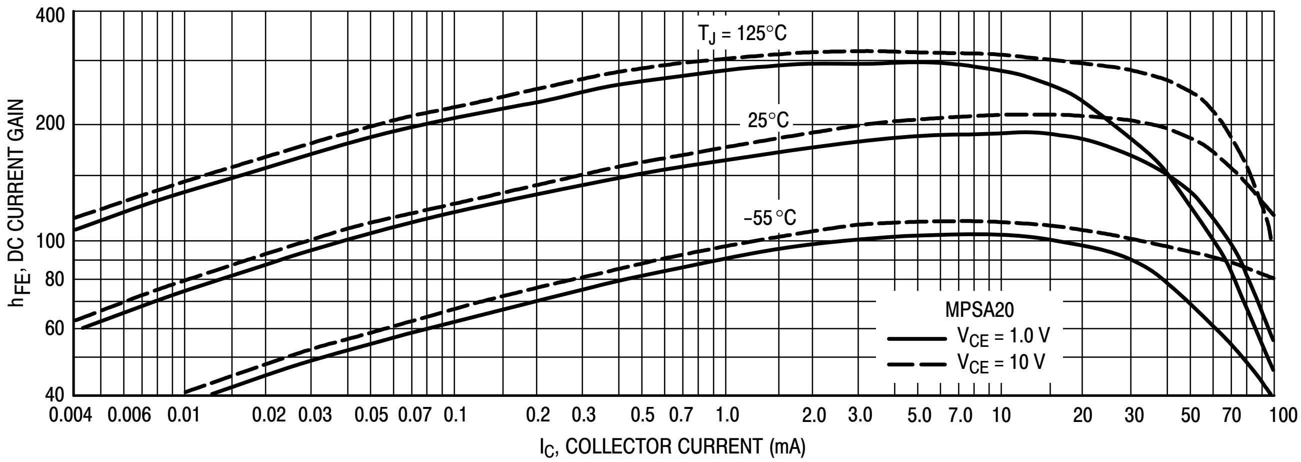


Figure 8. DC Current Gain

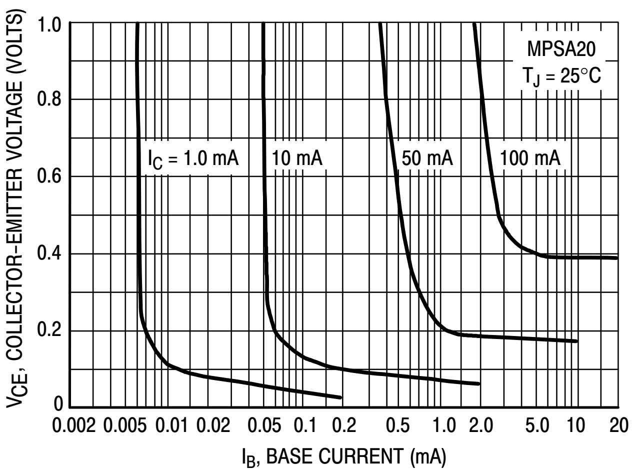


Figure 9. Collector Saturation Region

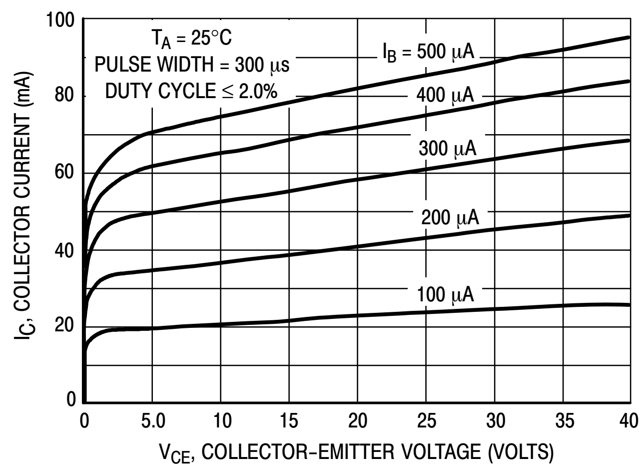


Figure 10. Collector Characteristics

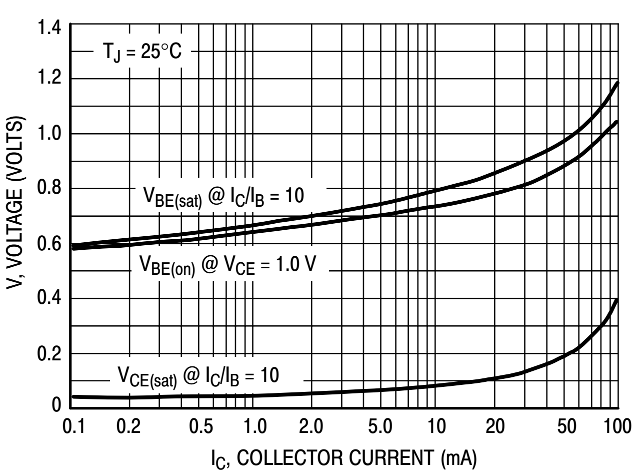


Figure 11. "On" Voltages

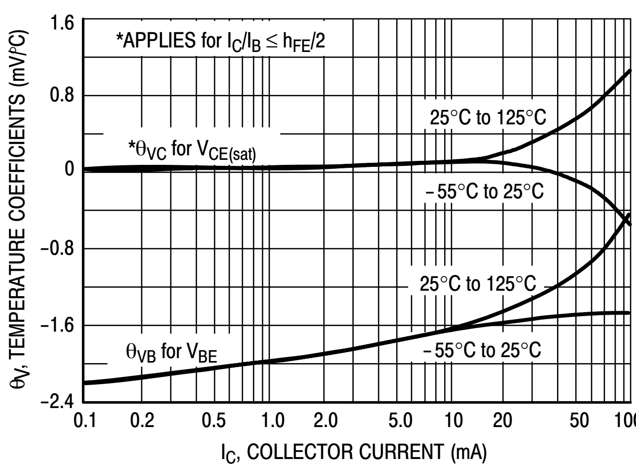


Figure 12. Temperature Coefficients

TYPICAL DYNAMIC CHARACTERISTICS

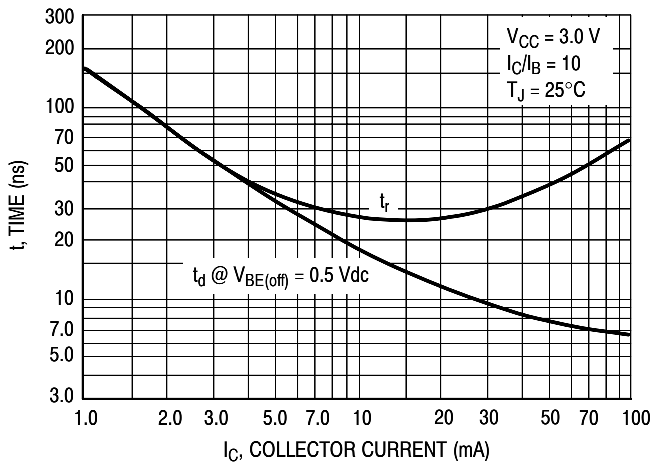


Figure 13. Turn−On Time

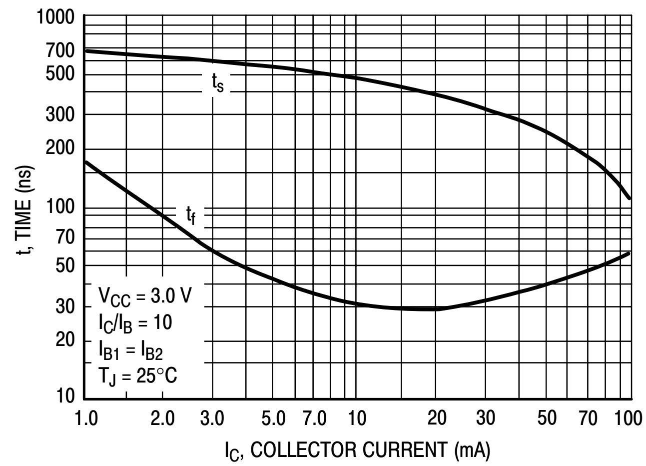


Figure 14. Turn−Off Time

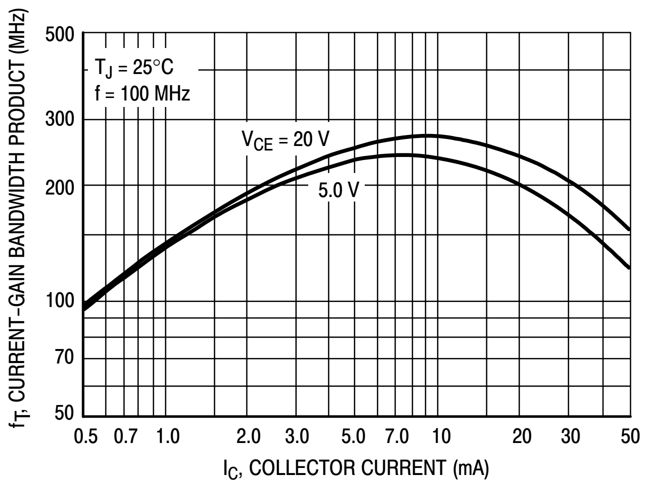


Figure 15. Current−Gain − Bandwidth Product

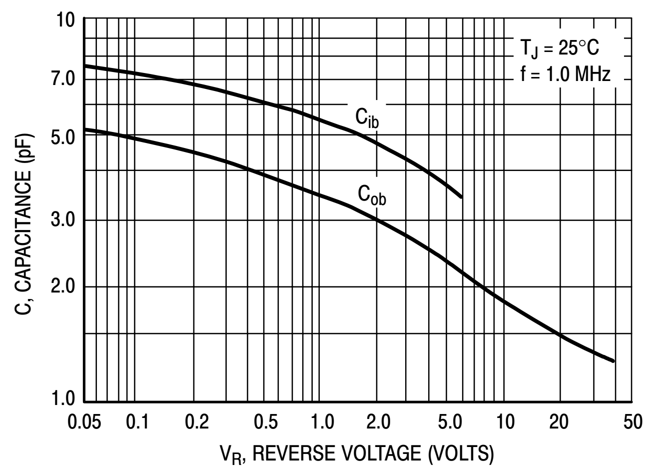


Figure 16. Capacitance

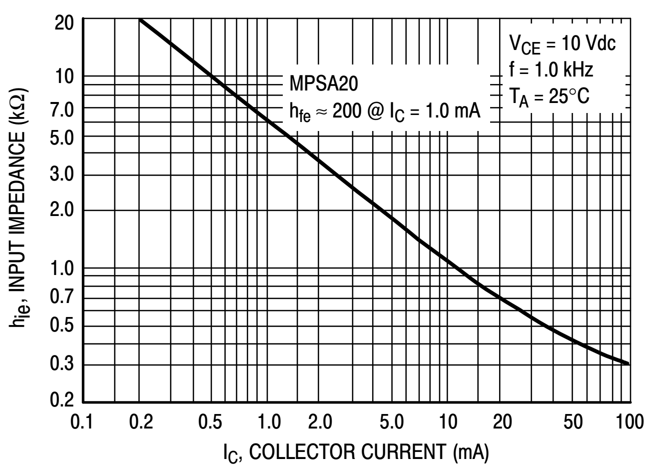


Figure 17. Input Impedance

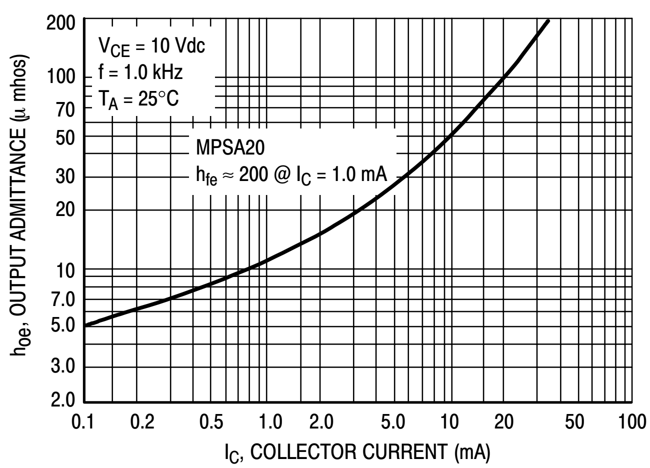


Figure 18. Output Admittance

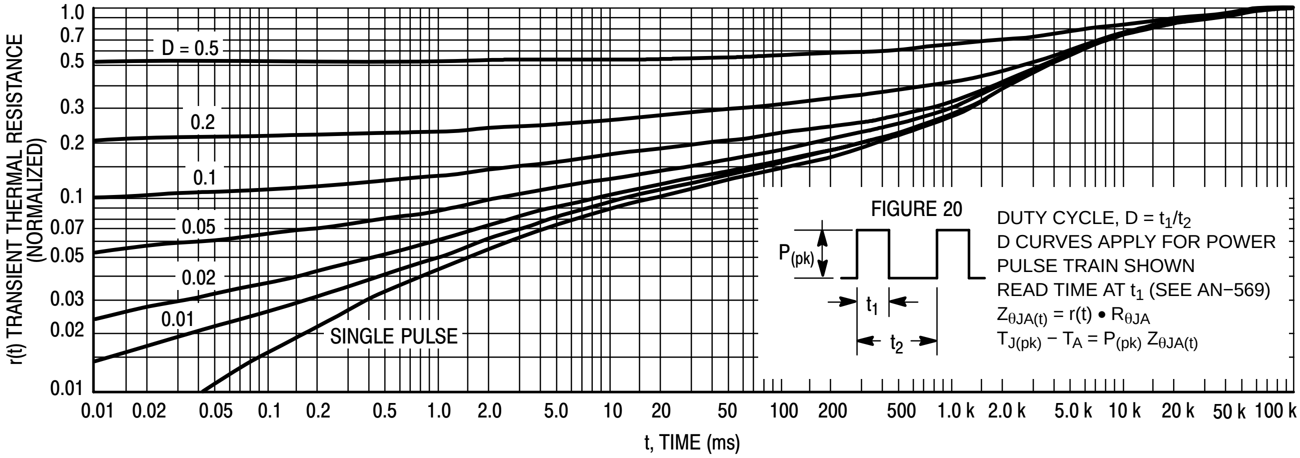


Figure 19. Thermal Response

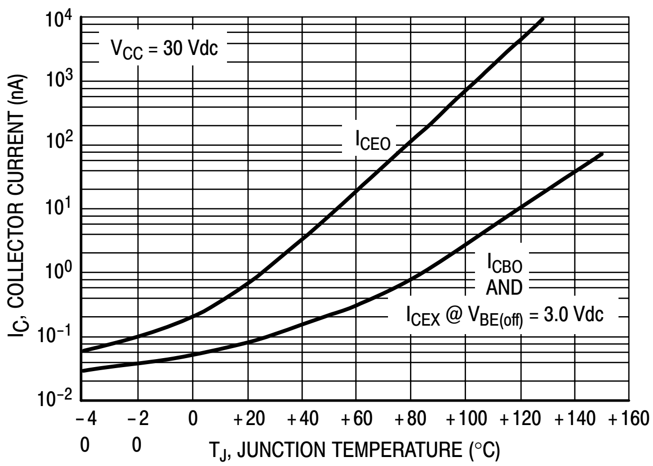


Figure 21.

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 20. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 19 was calculated for various duty cycles.

To find $Z_{\theta JA(t)}$, multiply the value obtained from Figure 19 by the steady state value $R_{\theta JA}$.

Example:

Dissipating 2.0 watts peak under the following conditions:

t_1 = 1.0 ms, t_2 = 5.0 ms. (D = 0.2)

Using Figure 19 at a pulse width of 1.0 ms and D = 0.2, the reading of r(t) is 0.22.

The peak rise in junction temperature is therefore

$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88°C.$

For more information, see ON Semiconductor Application Note AN569/D, available on our website at **www.onsemi.com**.

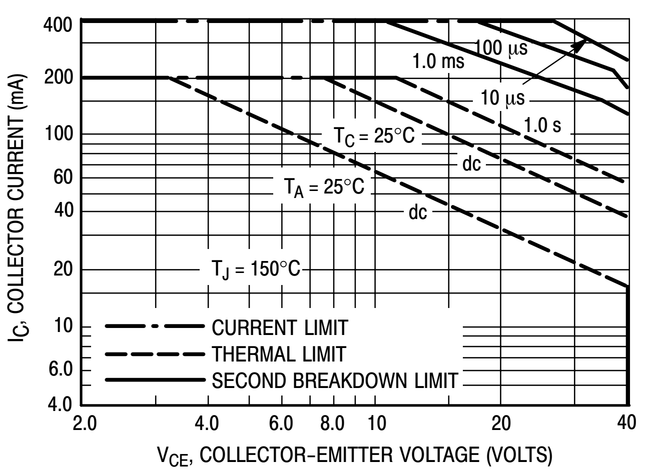


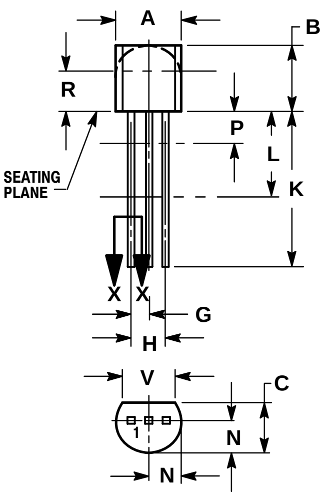
Figure 22.

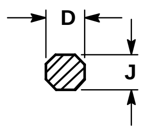
The safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 22 is based upon $T_{J(pk)}$ = 150°C; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq$ 150°C. $T_{J(pk)}$ may be calculated from the data in Figure 19. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

PACKAGE DIMENSIONS

TO−92 (TO−226)
CASE 29−11
ISSUE AL





SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.